

SEMICONDUCTOR DEVICE

Publication number: JP2003174161 (A)

Publication date: 2003-06-20

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Classification:

- international: H01L29/78; H01L29/786; H01L29/86; (IPC1-7): H01L29/78; H01L29/786

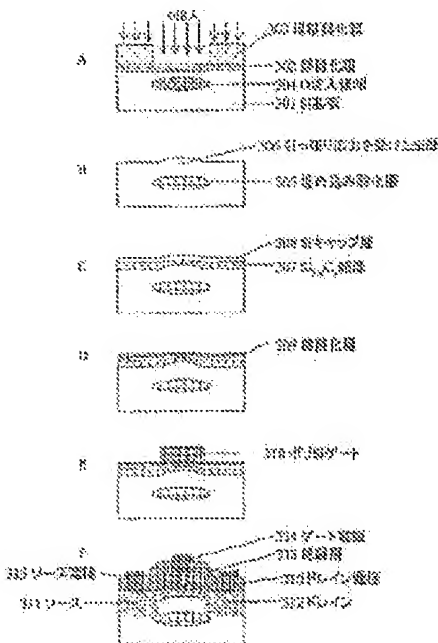
- European:

Application number: JP20010371257 20011205

Priority number(s): JP20010371257 20011205

Abstract of JP 2003174161 (A)

PROBLEM TO BE SOLVED: To provide a structure of a semiconductor device using group IV crystal containing C, and to provide its manufacturing method. ; SOLUTION: Embedded oxide is formed in a Si substrate and SiGeC crystal is deposited on Si above it to improve the performance of a MOS transistor. ; COPYRIGHT: (C)2003,JPO



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